

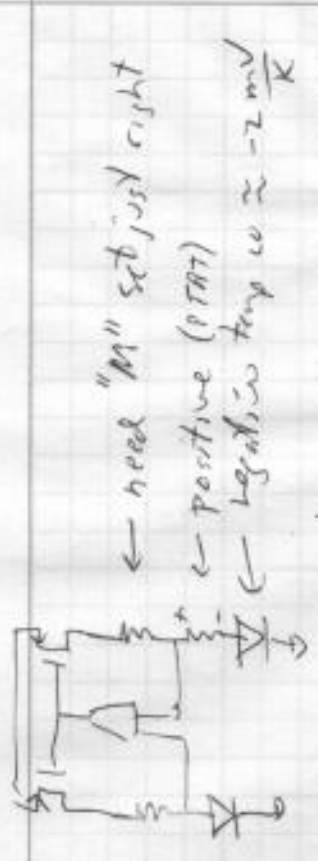
Project

- Wafer sort
- probe machine
- probe card
- laser trim
- digital trim - OTP, flash

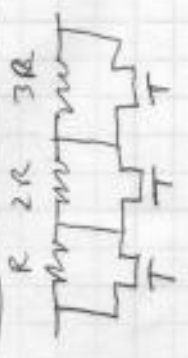
- telescopic cascode
- folded cascode
- high swing biasing
- switched capacitors

Lab 4

Device modeling
 correction from last lecture
 LVT not Φ VT



one of many clever ways to set BG voltage



how to set R_i ?
 measure and trim w/ LASER (old)
 digitally programmed (today)

Cascode axes

gain, bandwidth & stability, I/O range/swing.

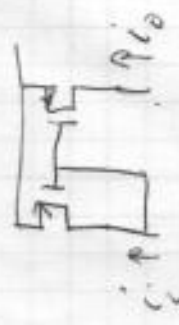
Simplest

telescopic cascode

(slide scanned in last lecture)

WIOLI

High-swing cascode micros

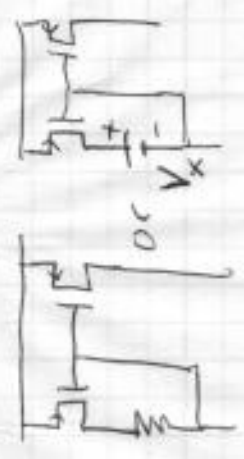


$$\frac{I_D}{I_i} = 1 + \frac{1}{5\mu\text{m}}$$

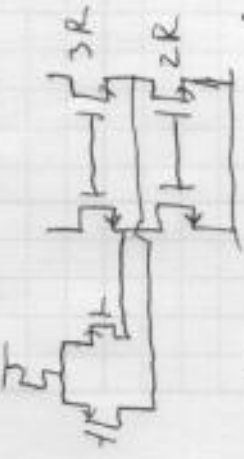
how big can R be and still have FET in saturation?

how big can V_x be? V_{tp}

$$I_D R < V_{tp} \text{ is fine}$$



Lets look at NMOS biasing

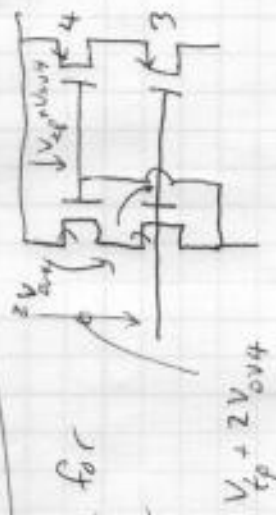


to maximize swing

choose V_{ov2} as small as possible (100mV for this class)

$$\Rightarrow V_{G2} = V_{in} + V_{ov2}$$

Choose V_{G3} st. $V_{S3} = V_{D2} \approx V_{ov2}$



use some trick for PMOS mirror

$$V_{tp} + 2V_{ov4}$$

why does this still work as a mirror?

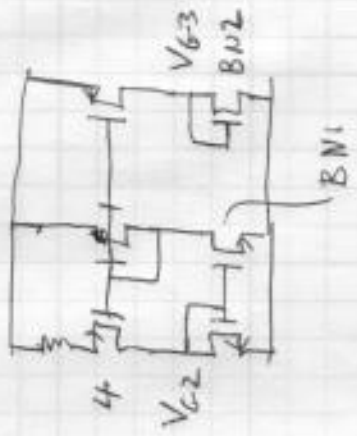


what is the gain from V_{G4} to V_{S3} ?

$$G_m \approx g_{m4} \quad R_O \approx \frac{1}{g_{m3}}$$

$$A_v = -\frac{g_{m4}}{g_{m3}} = -1$$

$$V_{G3} = V_{in} + V_{ov3} + V_{ov2} + \text{margin}$$



if $(\frac{W}{L})_{BN2} = \frac{1}{4} (\frac{W}{L})_{BN1}$

then $V_{ovBN2} = V_{ovBN1}$

if currents are same, then $\frac{2}{1}$

Safer to choose $\frac{1}{5}, \frac{1}{6}$

4LR specify the current

3LR let it flow through

why do we need 3L?

Don't, but keeps $V_{D4LR} \approx \text{same}$

" $I_{D4LR} \approx \text{same}$